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(54) LASER ANNEALING METHOD AND LASER ANNEALING DEVICE

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ABSTRACT

In order to promote an effect of laser annealing in respect of a semiconductor film, moisture is intentionally included in an atmosphere in irradiating laser beam to the semiconductor film by which a temperature holding layer comprising water vapor is formed on the surface of the semiconductor film in irradiating the laser beam and the laser annealing operation can be performed effectively.

47 Claims, 9 Drawing Sheets

